

361-975

POWER TRANSISTORS

2N3055H, 2N6253, 2N6254, 2N6371, 40251 Hometaxial-Base High-Power Silicon N-P-N Transistors

Rugged, Broadly Applicable Devices For Industrial and Commercial Use

These RCA types are silicon n-p-n transistors intended for a wide variety of high-power linear and switching applications. The hometaxial-base construction of these devices makes them highly resistant to second breakdown; for example, the 2N3055H can withstand an $I_{S/b}$ current of

1.95 amperes (min.) at a V_{CEO} of up to 60 volts. For the 2N6254, the $I_{S/b}$ rating is 1.87 amperes (min.) at V_{CEO} up to 80 volts.

All of these transistors are supplied in the JEDEC TO-3 hermetic steel package.

Features:

- 2N6254: premium type from 2N3055H family
- Maximum safe-area-of-operation curves
- Low saturation voltages
- High dissipation ratings
- Thermal-cycle rating curves

Applications:

- Series and shunt regulators
- High-fidelity amplifiers
- Power-switching circuits
- Solenoid drivers
- Low-frequency inverters

MAXIMUM RATINGS, Absolute-Maximum Values:

	2N3055H	2N6253	2N6254	2N6371	40251	
* V_{CBO}	100	55	100	50	50	V
* $V_{CER(sus)}$ $R_{BE} = 100 \Omega$	70	55	85	45	—	V
* $V_{CEO(sus)}$	60	45	80	40	40	V
$V_{CEV(sus)}$ $V_{BE} = -1.5 V$	90	55	90	50	50	V
* V_{EBO}	7	5	7	5	5	V
* I_C	15	15	15	15	15	A
* I_B	7	7	7	7	7	A
* P_T $\leq 25^\circ C$	115	115	150	117	117	W
$> 25^\circ C$	Derate linearly to $200^\circ C$					
* T_J, T_{stg}	—65 to +200					$^\circ C$
* T_L During soldering, at distances 1/32 in (0.8 mm) from seating plane for 10 s max	235					$^\circ C$

*In accordance with JEDEC registration data formats JS-9 RDF-10, 2N3055H; JS-6 RDF-2; 2N6253, 2N6254, 2N6371.

TERMINAL DESIGNATIONS

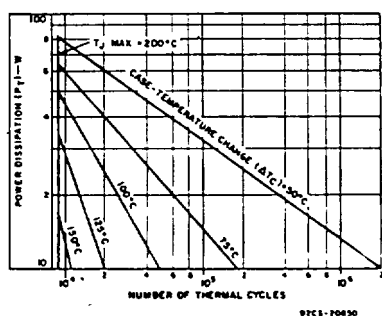
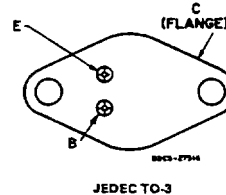


Fig. 1 - Thermal-cycling rating chart for 2N3055H, 2N6253, 2N6371.

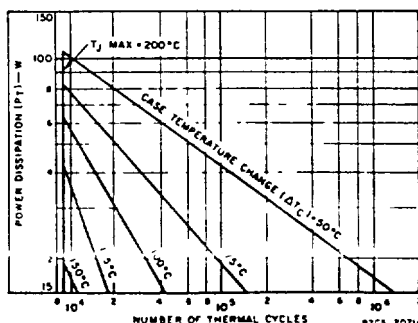


Fig. 2 - Thermal cycling rating chart for 2N6254.

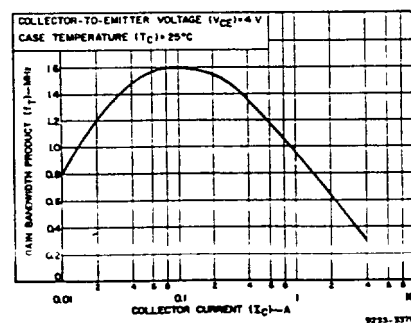


Fig. 3 - Typical gain-bandwidth product for all types

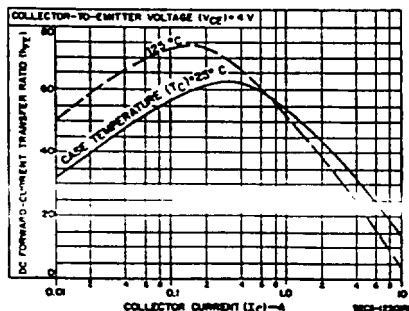


Fig. 4 - Typical dc beta characteristics for 2N3055H and 2N6371

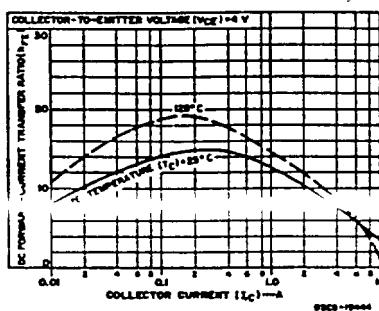


Fig. 5 - Typical dc beta characteristics for 2N6254.

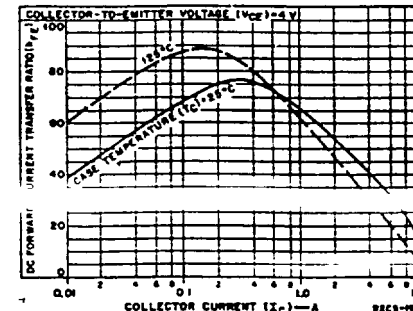


Fig. 6 - Typical dc beta characteristics for 2N6254.

SEMELAB LIMITED

POWER TRANSISTORS

2N3055H, 2N6253, 2N6254, 2N6371, 40251

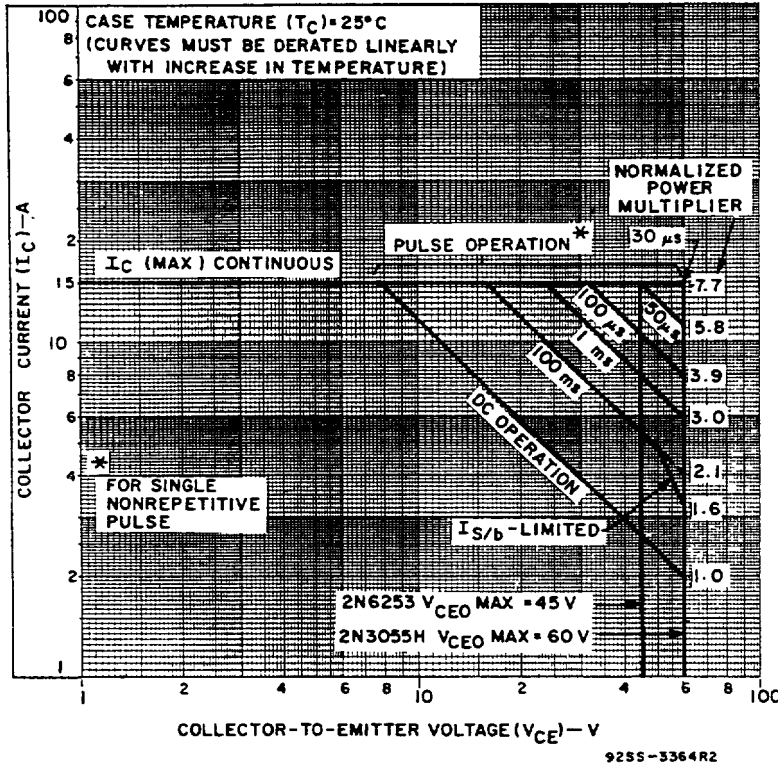


Fig 7 - Maximum operating areas for types 2N6253 and 2N3055H

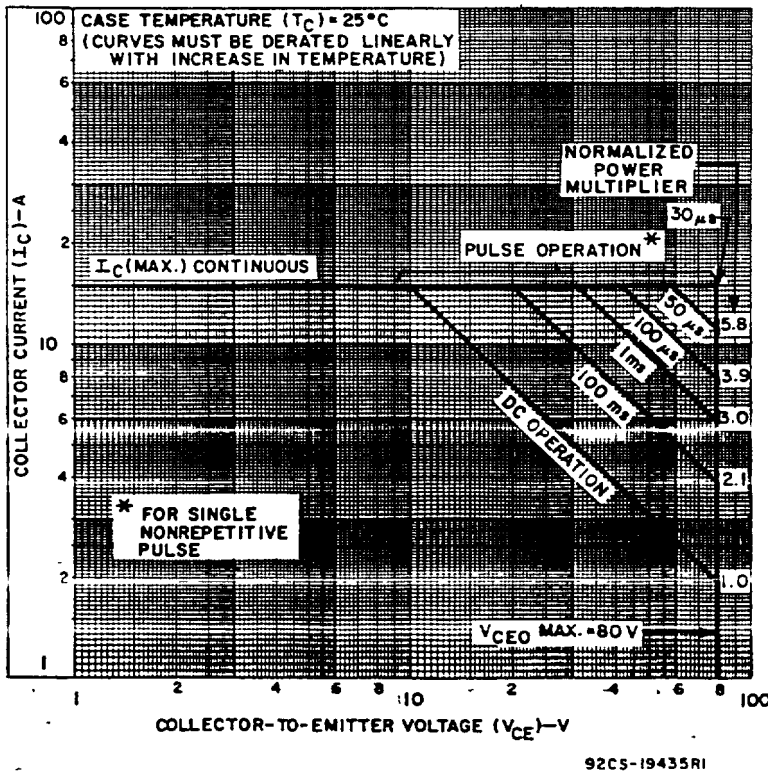


Fig 10 - Maximum operating areas for 2N6254.

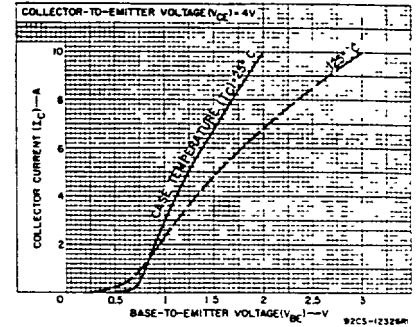


Fig 8 - Typical transfer characteristics for 2N6254, 2N3055H, 2N6371, 40251.

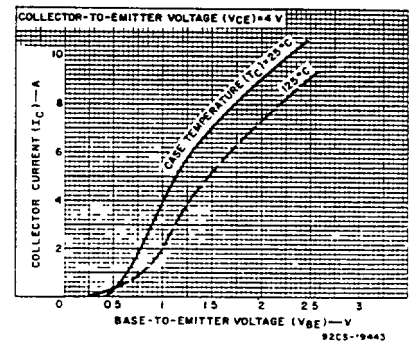


Fig 9 - Typical transfer characteristics for 2N6253

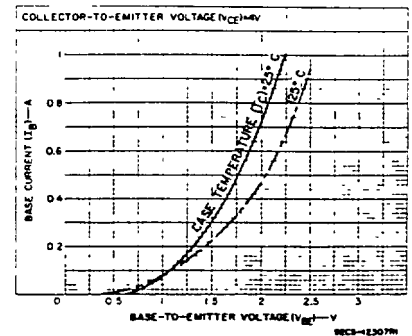


Fig 11 - Typical input characteristics for 2N3055H, 2N6371, 40251.

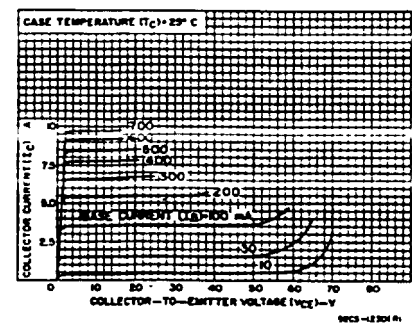


Fig 12 - Typical output characteristics for 2N3055H, 2N6371

2N3055H, 2N6253, 2N6254, 2N6371, 40251

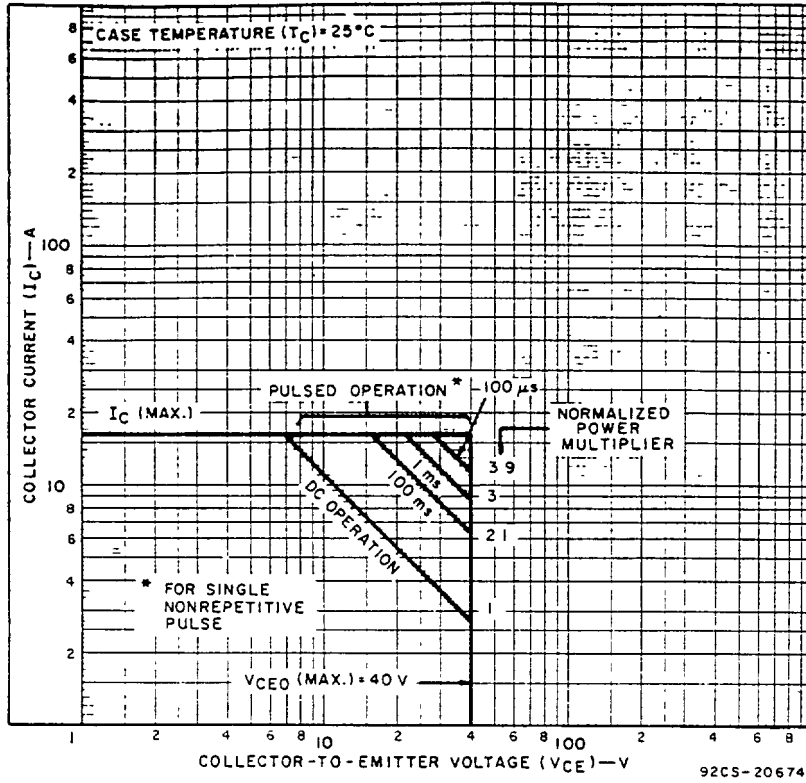


Fig. 13 - Maximum safe area of operation at case temperature of 25°C for 2N6371.

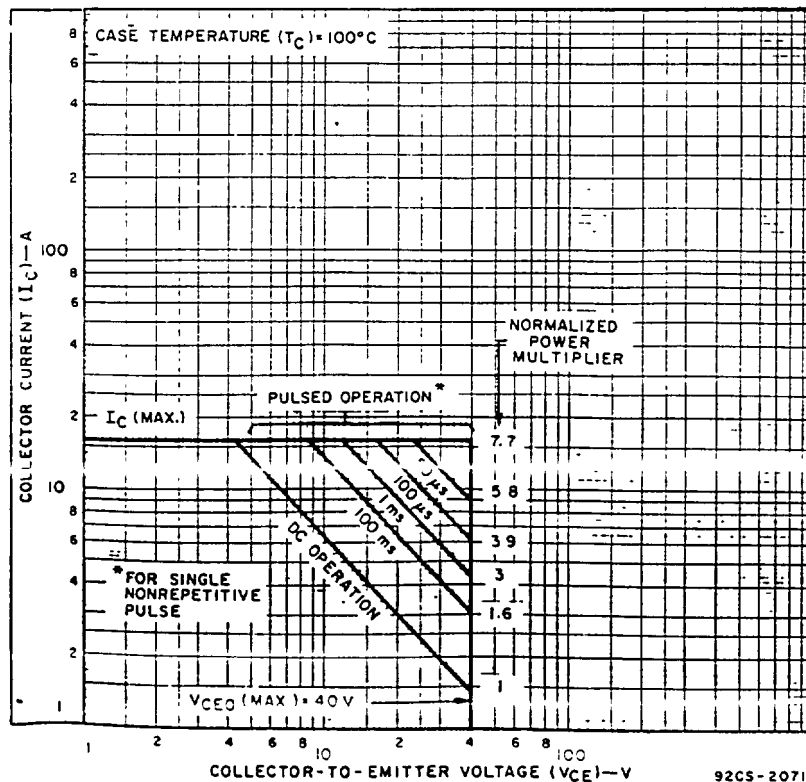


Fig. 16 - Maximum safe area of operation at case temperature of 100°C for 2N6371.

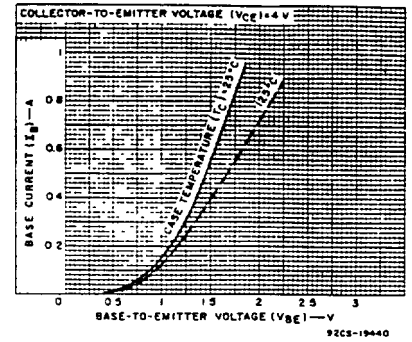


Fig. 14 - Typical input characteristics for 2N6253.

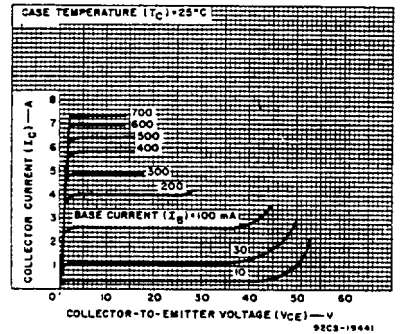


Fig. 15 - Typical output characteristics for 2N6253.

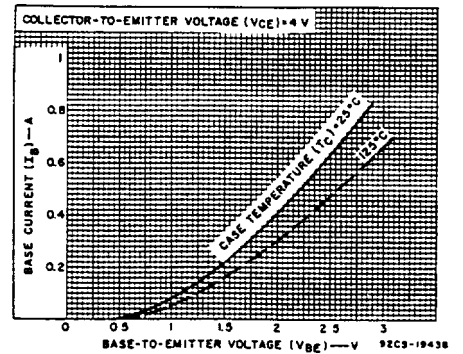


Fig. 17 - Typical input characteristics for 2N6254.

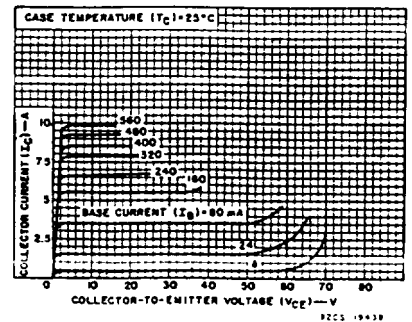


Fig. 18 - Typical output characteristics for 2N6254.

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2N3055H, 2N6253, 2N6254, 2N6371, 40251

ELECTRICAL CHARACTERISTICS, $T_C = 25^\circ\text{C}$ Unless Otherwise Specified.

CHARACTERISTIC	TEST CONDITIONS				LIMITS										UNITS
	VOLTAGE		CURRENT		2N3055H		2N6253		2N6254		2N6371		40251		
	V _{dc}	V _{dc}	A _{dc}	A _{dc}	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
	V _{CE}	V _{BE}	I _C	I _B											
I _{CEO}	25			0	-	-	-	1.5	-	-	-	1.5	-	-	mA
	30			0	-	0.7	-	-	-	-	-	-	-		
	60			0	-	-	-	-	-	1	-	-	-		
I _{CEX}	40	-1.5			-	-	-	-	-	-	-	-	2	mA	
	45	-1.5			-	-	-	-	-	-	-	2			
	55	-1.5			-	-	-	2	-	-	-	-	-		
	100	-1.5			-	5	-	-	-	0.5	-	-	-		
T _C = 150°C	40	-1.5			-	-	-	-	-	-	-	10	10		
	50	-1.5			-	-	-	10	-	-	-	-	-		
	100	-1.5			-	30	-	-	-	5	-	-	-		
I _{EBO}		-5			-	-	-	10	-	-	-	-	-	mA	
		-7			-	5	-	-	-	0.5	-	-	-		
V _{(BR)CBO}			0.1		-	-	-	-	-	-	-	50	-	V	
V _{(BR)CEV}		-1.5	0.1		-	-	-	-	-	-	-	50	-	V	
V _{(BR)EBO} I _E = 0.01 mA			0		-	-	-	-	-	-	-	5	-	V	
V _{CEO(sus)}			0.2 ^a	0	60	-	45	-	80	-	40	-	40	V	
V _{CER(sus)} R _{BE} = 100 Ω			0.2 ^a		70	-	55	-	85	-	45	-	-		
V _{CEV(sus)}		-1.5	0.1 ^a		90	-	55	-	90	-	50	-	-		
h _{FE}	4		3 ^a		-	-	20	70 ^c	-	-	-	-	-		
	4		4 ^a		20	70	-	-	-	-	-	-	-		
	2		5 ^a		-	-	-	-	20	70	-	-	-		
	4		8 ^a		-	-	-	-	-	-	15	60	15		60
	4		10 ^a		5	-	-	-	-	-	-	-	-		-
	4		15 ^a		-	-	3	-	5	-	-	-	-		-
	4		16 ^a		-	-	-	-	-	-	4	-	-		-
V _{BE}	4		3 ^a		-	-	-	1.7	-	-	-	-	-	V	
	4		4 ^a		-	1.8	-	-	-	-	-	-	-		
	2		5 ^a		-	-	-	-	-	1.5	-	-	-		
	4		8 ^a		-	-	-	-	-	-	-	-	2.2		
	4		16 ^a		-	-	-	-	-	-	4	-	-		
V _{CE(sat)}			3 ^a	0.3 ^a	-	-	-	1	-	-	-	-	-	V	
			4 ^a	0.4 ^a	-	1.1	-	-	-	-	-	-	-		
			5 ^a	0.5 ^a	-	-	-	-	-	0.5	-	-	-		
			8 ^a	0.8 ^a	-	-	-	-	-	-	1.5	-	1.5		
			10 ^a	3.3 ^a	-	8	-	-	-	-	-	-	-		
			15 ^a	3 ^a	-	-	-	-	-	4	-	-	-		
			15 ^a	5 ^a	-	-	-	4	-	-	-	-	-		
		16 ^a	4 ^a	-	-	-	-	-	-	4	-	-			
h _{fe} f = 1 kHz	4		1		15	120	10	-	10	-	10	-	-		
f _T			1		800	-	-	-	-	-	800	-	-	kHz	
h _{fe} l f = 0.4 MHz	4		1		-	-	2	-	2	-	2	-	-		
f _{hfe}	4		1		10	-	10	-	10	-	-	-	-	kHz	
S/b t _p = 1 s nonrep.	39				-	-	-	-	-	-	-	3	-	A	
	40				2.9	-	-	-	-	-	2.9	-	-		
	45				-	-	2.55	-	-	-	-	-	-		
	60				1.95	-	-	-	-	-	-	-	-		
	80				-	-	-	-	1.87	-	-	-	-		
θ _{JC}					-	1.5	-	1.5	-	1.17	-	1.5	-	°C/W	

* In accordance with JEDEC registration data formats JS-9 RDF 10 2N3055H JS-6 RDF 2 2N6253 2N6254 2N6371

^a pulse, pulse duration = 300 μs, duty factor = 1.8%